PAN0080H

N-Ch 100V Fast Switching MOSFET

V_{DS}=100V, I_D=2.3A ,$RDS_{(ON)}$=285mΩ

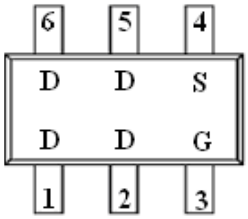
➢ General Description

This PAN0080H N-Channel enhancement mode power field effect transistor is the high density trench technology and this advanced technology can provide excellent Rds(On) performance and efficiency for power switching and load switching application., this device also comply with the RoHS and Green Product requirement with full function reliability approved.

➢ Feature

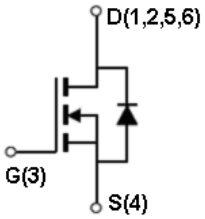
●Low Offset (Error) Voltage
●Low-Voltage Operation
●High-Speed Circuits
●Low Battery Voltage Operation
●SOT-363 package design

➢ SOT-363



➢ Application

●Drivers: Relays, Solenoids, Lamps,
Hammers, Displays, Memories
●Battery Operated Systems
●Load/Power Switching Smart Phones, Pagers
●PA Switch
●Level Switch



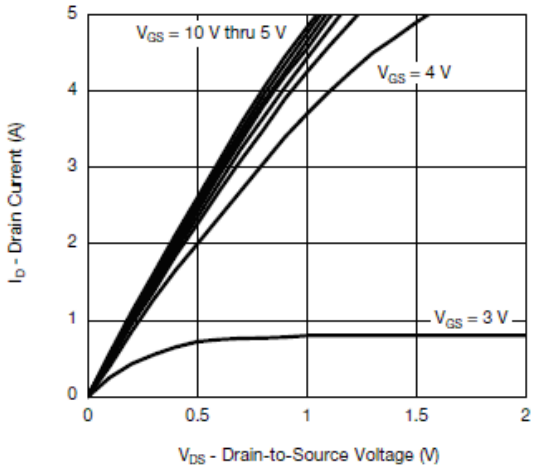
➢ Absolute Maximum Ratings

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	100	V
Gate –Source Voltage		V_{GSS}	±20	V
Continuous Drain Current(T_J=150℃)	T_A=25℃	I_D	2.3	A
	T_A=70℃		1.8	
Pulsed Drain Current		I_{DM}	7	A
Continuous Source Current(Diode Conduction)		I_S	1.3	A
Power Dissipation	T_A=25℃	P_D	1.5	W
	T_A=70℃		1.0	
Operating Junction Temperature		T_J	150	℃
Storage Temperature Range		T_{STG}	-55/150	℃
Thermal Resistance-Junction to Ambient		$R_{\theta JA}$	120	℃/W

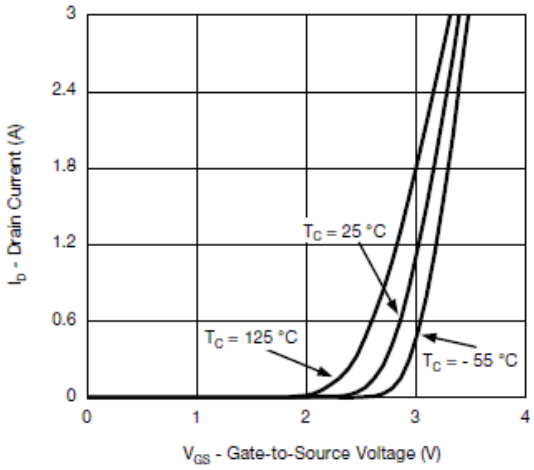
➢ Electrical Characteristics (T_A=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V,I_D=250uA	100			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250uA	1.0		2.0	
Gate Leakage Current	I_{GSS}	V_{DS}=0V,V_{GS}=±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=80V,V_{GS}=0V			1	uA
		V_{DS}=80V,V_{GS}=0V T_J=85℃			10	
On-State Drain Current	$I_{D(on)}$	V_{DS}≧5V,V_{GS}=4.5V	5			A
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V,I_D=2.3A		265	285	mΩ
		V_{GS}=4.5V,I_D=1.8A		275	295	
Forward Transconductance	g_{FS}	V_{DS}=20V,I_D=1.5A		2		S
Diode Forward Voltage	V_{SD}	I_S=1.3A,V_{GS}=0V		0.85	1.2	V
Dynamic						
Total Gate Charge	Q_g	V_{DS}=50V,V_{GS}=4.5V I_D≡1.6A		2.8	5.8	nC
Gate-Source Charge	Q_{gs}			0.75		
Gate-Drain Charge	Q_{gd}			1.4		
Input Capacitance	C_{iss}	V_{DS}=50V,V_{GS}=0V f=1MHz		200		pF
Output Capacitance	C_{oss}			22		
Reverse Transfer Capacitance	C_{rss}			13		
Turn-On Time	$t_{d(on)}$	V_{DD}=50V,R_L=39Ω I_D≡1.3A,V_{GEN}=4.5V R_G=1Ω		25	50	ns
	t_r			20	50	
Turn-Off Time	$t_{d(off)}$			15	30	
	t_f			10	25	

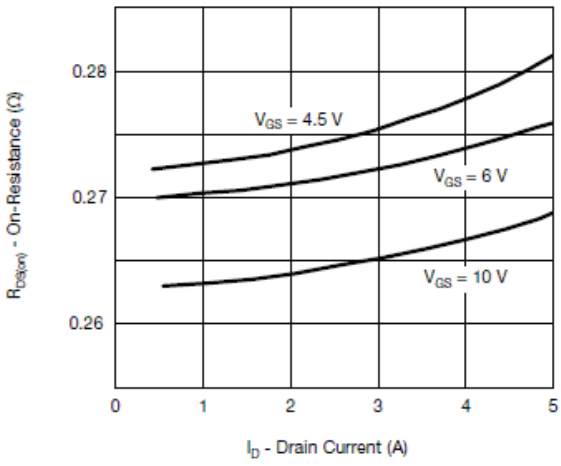
➢ Typical Characteristics



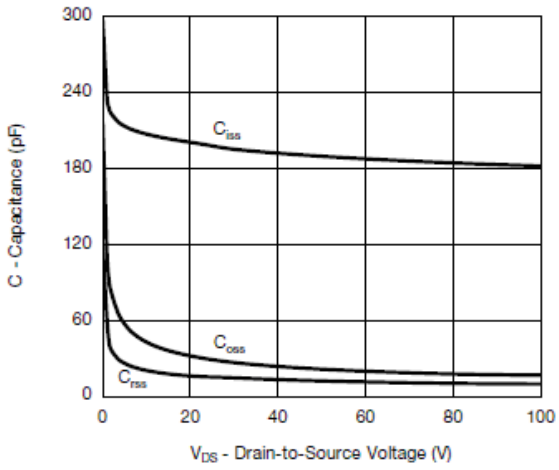
Output Characteristics



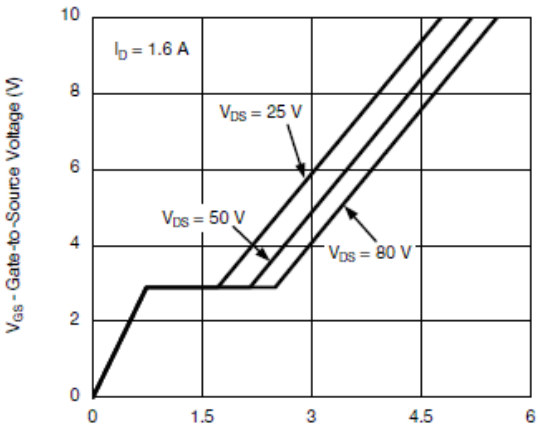
Transfer Characteristics



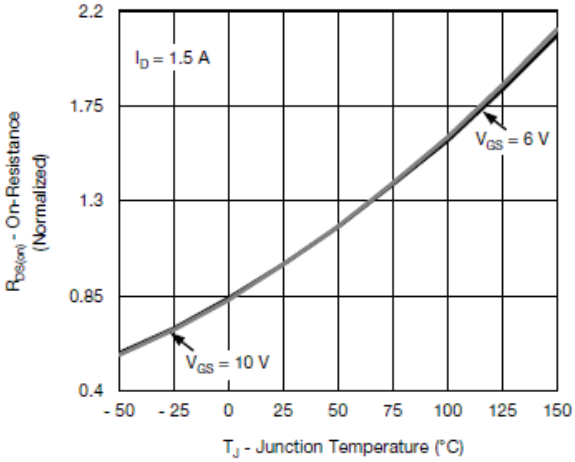
On-Resistance vs. Drain Current and Gate Voltage



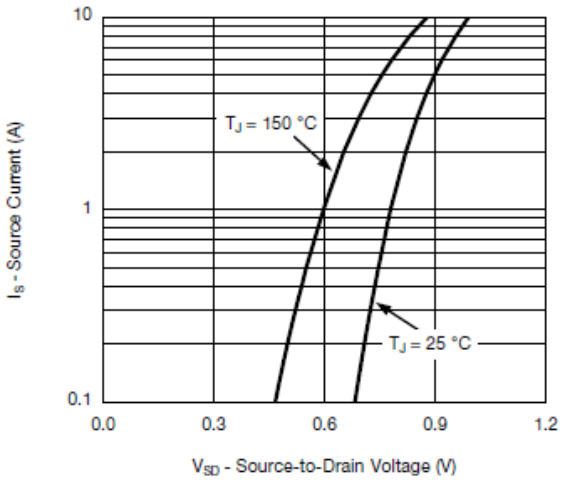
Capacitance



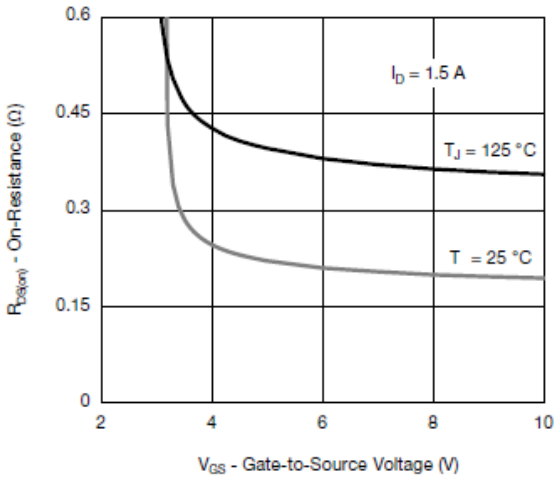
Gate Charge



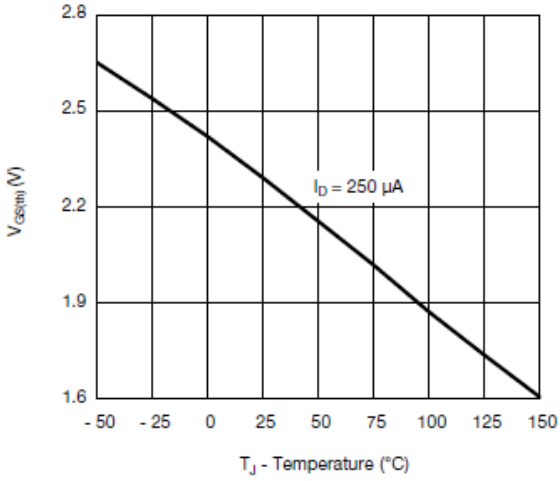
On-Resistance vs. Junction Temperature



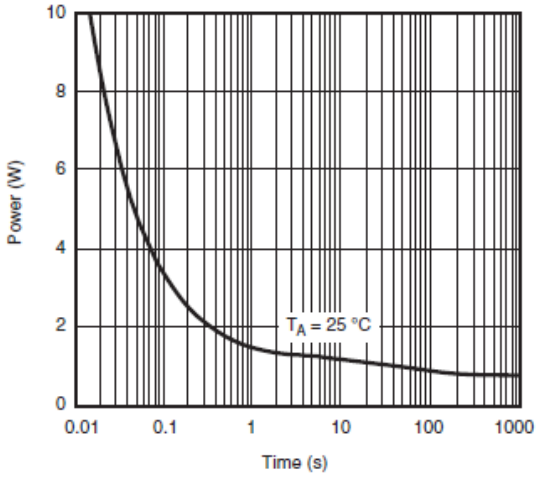
Source-Drain Diode Forward Voltage



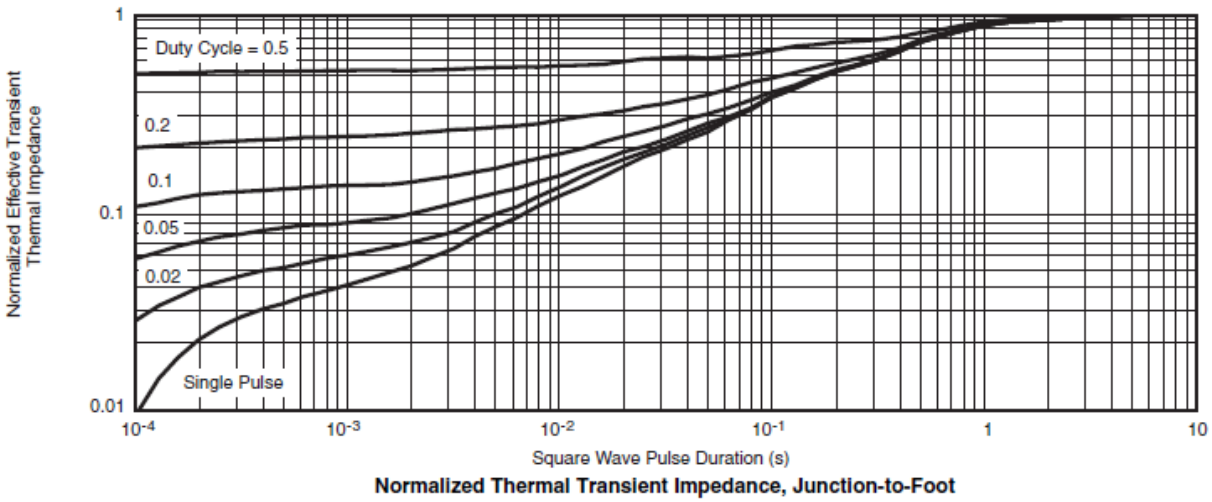
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

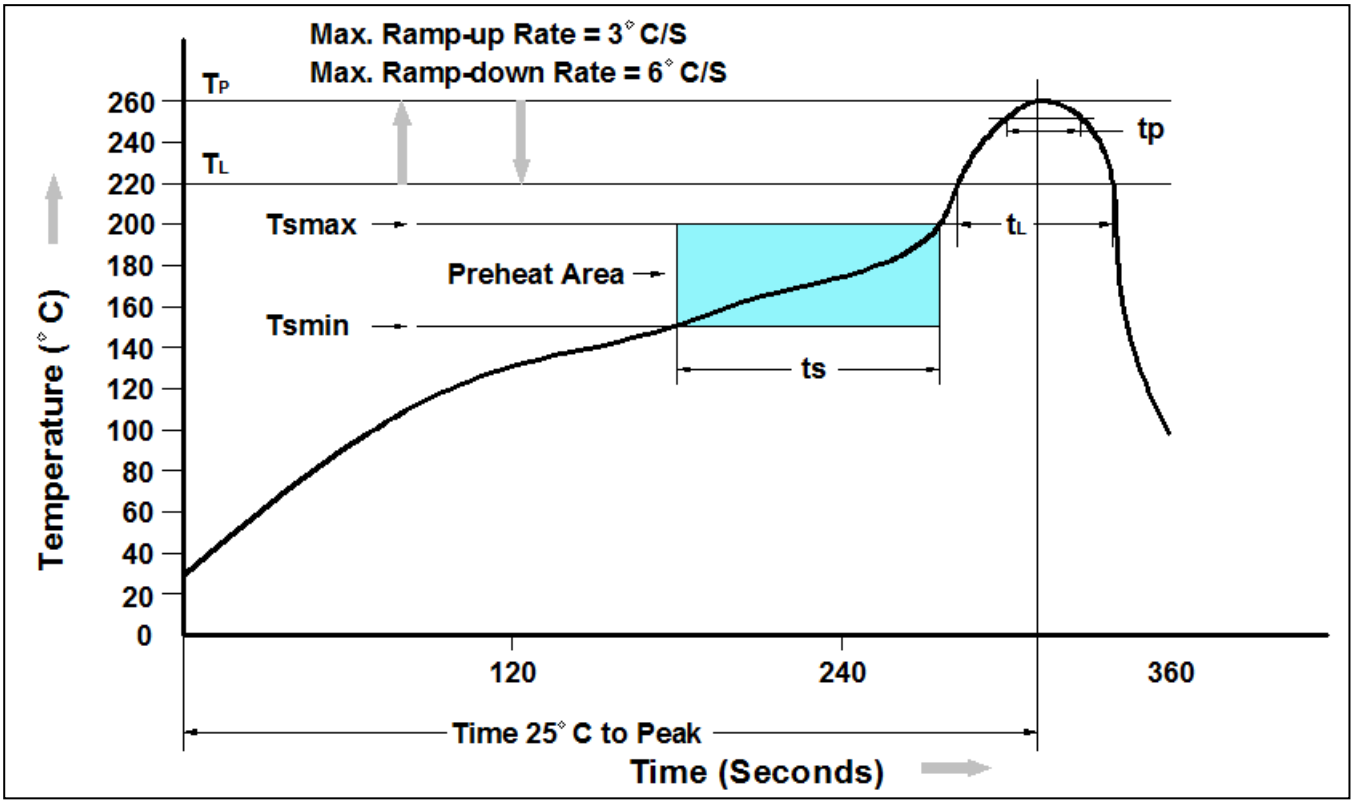


Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Foot

➢ Recommand IR Reflow Soldering Thermal Profile

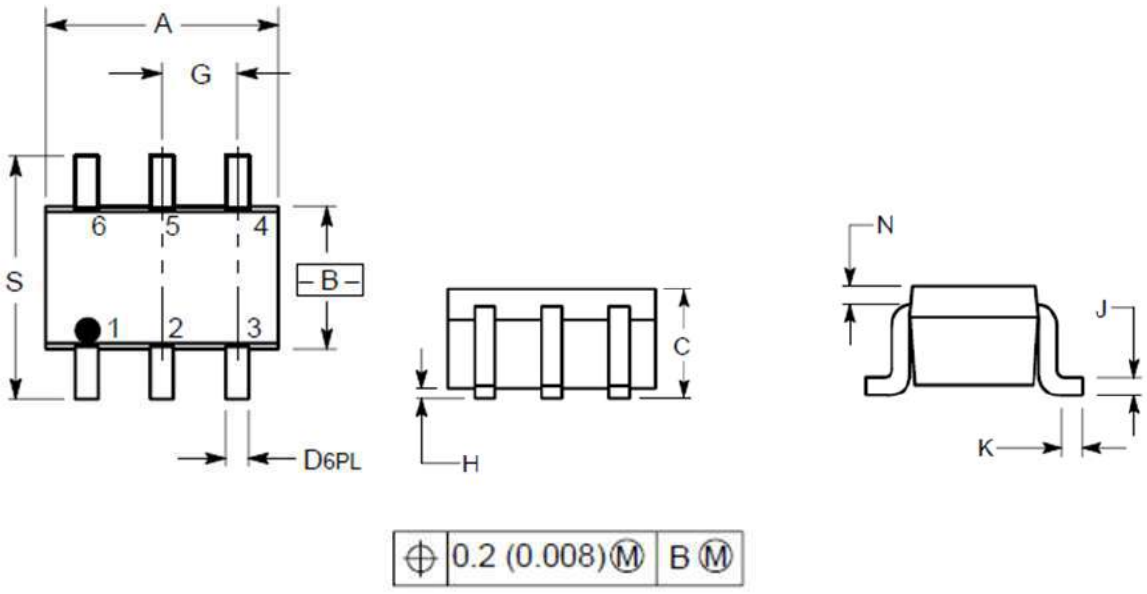


Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	150°C
Temperature Max. (Tsmax)	200°C
Time (ts) from (Tsmin to Tsmax)	60-120 seconds
Average Ramp-up Rate (tL to tP)	3°C/second max.
Liquidous Temperature (TL)	217°C
Time (tL) Maintained Above (TL)	60 – 150 seconds
Peak Temperature	260°C +0°C / -5°C
Time (tP) within 5°C of actual Peak Temperature	30 seconds
Ramp-down Rate (TP to TL)	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.

➢ Ordering Information

Part Number	Description	Quantity
PAN0080H	SOT-363 Reel	3000 pcs

➢ Package Information (SOT-363)



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026 BSC		0.65 BSC	
H	---	0.004	---	0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20 REF	
S	0.079	0.087	2.00	2.20

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